

# NEC's LOW POWER GPS RF RECEIVER

**UPB1008K** 

### **FEATURES**

- LOW POWER CONSUMPTION: 52 mW
- DUAL-CONVERSION IQ DOWN CONVERTER<sup>1</sup>: Reference frequency: REFin = 27 MHz
- PSEUDO-BASEBAND WITH 2-BIT DIGITIZED OUTPUT
- ON-CHIP LNA, ON-CHIP FREQUENCY SYNTHESIZER, IF AGC AMPLIFIER:

with 45 dB typical range of adjustable gain

SMALL 36 PIN QFN PACKAGE:
Flat lead style for better RF performance
Note:

1. Based on eRide's proprietary GPS DSP architecture

### **BLOCK DIAGRAM**



### **APPLICATIONS**

- E911 ENABLED MOBILE PHONE
- IN-VEHICLE NAVIGATION SYSTEMS
- LOW POWER HANDHELD GPS RECEIVER
- PC/PDA+GPS INTEGRATION
- ASSET TRACKING

### DESCRIPTION

NEC's UPB1008K is a Silicon RFIC especially designed for handheld low power/low cost GPS receivers. The IC combines an LNA, followed by a double-conversion RF/IF downconverter block and a PLL frequency synthesizer on one chip. The second IF Freqency is a pseudo- baseband signal into a on-chip 2-bit A/D converters. The device can operate on a supply voltage as low as 2.7 V, and is a housed in a small 36 pin QFN (Quad, Flat, No-lead) package, resulting in a very low power consumption and reduced board space.

NEC's stringent quality assurance and test procedures ensure the highest reliability and performance.



## **RF APPLICATION DIAGRAM**

California Eastern Laboratories

### ADVANCED GPS COMPLETE SOLUTION



### ADVANCED GPS COMPLETE SOLUTION

"NEC Corporation and eRide, Inc. have teamed to provide an advanced positioning solution delivering high GPS performance, accuracy, integration and architecture flexibility. The chip set combines CEL's **UPB1008K** receiver IC with eRide's **Opus One** SOC (System-on-a-Chip) Baseband ASIC and is suitable for standard GPS products as well as Cellular Handset applications. Also provided are scalable client navigation software and drivers, plus location-aiding data from eRide's Smart Server. Together, they offer a complete hardware/infrastructure solution.

The chip set's design allows it to operate independently of wireless interface standards - and independently of the host product's CPU and Operating System. This unique approach to system integration makes it easy to deploy the chip set into an wireless application, in any wireless network. A "Universal Hardware" solution, the design promises lower manufacturing costs and, ultimately lower cost to the consumer.

The chip set's advanced positioning architecture offers unmatched sensitivity providing fast, accurate positioning architecture offers unmatched sensitivity providing fast and accurate position fixes, even when indoors or in deep in urban canyons."

## HIGH PERFORMANCE GPS OMNI MODE

#### LI, C/A code receiver

Performance	Indoor	Outdoor
Time to First Fix w/ aiding	5-7sec	1-3sec
Time to First Fix w/o aiding	10-20sec	3-5sec
Accuracy	10-25m cep	2-5m cep
Sensitivity	-155dBm	-142dBm
	in 1sec dwells	in two 10msec dwells

Superior performance in high reflection indoor environments and in urban canyon types of outdoor environments

### **POWER DISSIPATION**

First Fix	400 mW
Tracking	200-300 mW
Stand By	30 mW

## ELECTRICAL CHARACTERISTICS (TA = 25°C, Vcc = 3.0 V, unless otherwise specified)

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
Icc	Total Circuit Current, No Signals	mA	14	18	23.5
Vcc	Supply Voltage	V	2.7	3.0	3.3
ICC_PD	Power down current, PIN 13 = VIL	μΑ	_	1	10
Icc rf	RF Block Circuit Current (pin 3), No signal	μΑ	0.4	0.5	0.7
Icc lo	VCO Block Circuit Current (pin 7), No signal	mA	4.1	5.6	7.2
ICC pll	PLL Block Circuit Current (pin 9), No signal	mA	2.7	3.6	4.7
ICC bb	Baseband Block Circuit Current (pin 23), No signal,	mA	2.5	3.4	4.3
	open load				
ICC if	IF Block Circuit Current (pin 28) , No signal	mA	2.7	3.7	4.7
ICC Ina	Pre-Amplifier Open Connector Current (pin 36), No signal	mA	1.0	1.4	1.8

#### LNA/RF DOWNCONVERTER

(fRFin = 1575.42 MHz, f1stLOin = 1400 MHz, PLO = -10 dBm, f1stIF = 175 MHz, Pin 13: VIL = 3 V, ZL differential = 32Ω & Zs = Γopt)

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
CGLNA_MIX	x Power conversion gain from 2nd LNA/mixer to 1st IF, PRFin = -50 dBm		18	23	28
NFLNA_MIX	x Noise Figure of 2nd LNA/mixer(SSB), Input matched dB		-	5	-
P1dBLNA_MIX	1 dB Compression refer to source, Input matched	Compression refer to source, Input matched dBm –		-38	-
ZLNAin	RF Input Impedance of LNA	Ohm –		31	-
ZMIXout	IF Output Impedance of Mixer	Ohm		32	
Alo-IF	Local Signal Leak to IF, f1stLOin=1400 MHz, PLO = 0 dBm	dBm	_	-35	_
ALO-RF	Local Signal Leak to RF, f1stLOin=1400 MHz, PLO = 0 dBm	dBm	-	-50	-

#### PLL

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
Ісрон	PLL Charge Pump High Side Current @ VCPout = VCC/2	μΑ	-	200	-
ICPOL	PLL Charge Pump Low Side Current @ VCPout = VCC/2	μΑ	-	-200	-
fPD	Phase Comparison Frequency	MHz	-	13.5	-

#### CRYSTAL OSCILLATOR/REVERENCE AMPLIFIER BLOCK

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
VREFin	Reference input minimum level	mVpp	50	200	-
fref	Input Frequency of Reference Input	MHz	_	27	_
VT	VCO Control Voltage, PLL Locked	V	0.8	1.5	2.2
C/N	VCO C/N, $\triangle$ 1kHz, Loop band width = 5 kHz	dBc/Hz	57	62	_

AGC AMPLIFIER, I-Q DEMODULATOR, and ADC BLOCK(f1stlFin = 175 MHz, Zin = 600Ω)

SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
CGAGC/MIX	Maximum voltage conversion gain of AGC amplifier/ I-Q mixer, Pin = -60 dBm, VAGC = 0.5 V, Unmatched	dB	_	30	-
	Minimum voltage conversion gain of AGC amplifier/ I-Q mixer, Pin = -60 dBm, VAGC = 2.0 V, Unmatched	dB	_	-15	-
AAGC/MIX	AGC control range, $V_{AGC} = 0.5 V$ to 2 V	dB	25	45	-
P1dBAGC	1 dB compression input to AGC amplifier, set voltage gain = 30 dB	dBm	_	-45	_
VAGC	AGC control voltage	V	0.5	-	2.0
BW	3dB Mixer Bandwidth	MHz	-	10	-
VIQ-C	IQ BalanceControl Voltage, Gain(Ich) = Gain (Qch)	V	-	2.1	2.8
AIQ-C	IQ Balance Control Gain Range, VIQ-C = 0 to 3 V	dB	4.0	6.5	-
Duty Ich	Ich Mag Bit Output Pulse Duty, P1stIFin = -84 dBm $V_{AGC} = 0.5 V$ , VIQ-C = 0 V	%	50	_	-
Duty Qch	Qch Mag Bit Output Pulse Duty, PIF2in = -88 dBm VAGC = 0.5 V, VIQ-C = 0 V	%	50	-	-
BASEBA	<b>ND AMPLIFIER BLOCK</b> (Zs = $2k\Omega \& ZL = 2 k\Omega$ )				
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
Vввон	Baseband output logic high, CL = 10 pF	V	2.0	-	-
VBBOL	Baseband output logic low, CL = 10 pF	V	0	-	0.5

## ABSOLUTE MAXIMUM RATINGS<sup>1,2</sup> (TA = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
Vcc	Supply Voltage <sup>4</sup>	Vcc	3.6
PD	Total Power Dissipation <sup>3</sup>	mW	361
Тор	Operating Temperature	°C	-40 to +85
Тѕтс	Storage Temperature	°C	-55 to +150
ICC_total	Total Circuit Current <sup>4</sup>		

#### Notes:

1. Operation in excess of any one of these parameters may result in permanent damage.

- 2. More than two items must not be reached simultaneously.
- 3. TA =  $+85^{\circ}$ C, mounted on a 50 x 50 x 1.6 mm double-sided copper clad epoxy glass PWB.
- 4. TA = 25°C

### RECOMMENDED OPERATING CONDITIONS

SYMBOLS	PARAMETERS	UNITS	MIN	ТҮР	MAX
Vcc	Supply Voltage	V	2.7	3.0	3.3
Тор	Operating Temperature	°C	-40	+25	+85
fRFin	RF Input Frequency	MHz		1575	
fREFin	Reference Frequency	MHz		27	
f1stLO	1st LO Oscillating				
	Frequency	MHz		1400	
f1stlFin	1st IF Input Frequency	MHz		175	
f2ndLOin	2nd LO Input Frequency	MHz		175	
Vін	Power Down Control				
	Voltage "High"	V	2		Vcc
VIL	Power Down Control				
	Voltage "Low"	V	0		0.5

## **APPLICATION CIRCUIT**



## UPB1008K

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
1	GNDIna LNAin	Ground pin of LNA Input pin of low noise amplifier. It is a single-ended open collector design. Capacitive coupling is required; external matching will improve gain or NF.	2D 2D 2D 2D 2D 2D 2D 2D 2D 2D
3	VCCrf	Supply voltage pin of LNA, RF mixer and VCO voltage regulator.	79
4	GNDlo	Ground pin of 1st LO Oscillator circuit and RF Mixer.	3 r=300 ≤ <u>a</u> <u>a</u> ≤ r=300
56	1stLO-OSC1 1stLO-OSC2	Pin 5 & 6 are base pins of the differential amplifier for 1st LO oscillator. These pins require an LC (varacator) tank circuit to oscillate at around 1400 MHz.	
7	VCClo	Supply voltage pin of oscillator circuit for 1st LO Oscillator and RF mixer	Regulator GND 4
8	PDout	This is a current mode charge pump output. For connection to a passive RC loop filter for driving external varactor diode of 1stLO-OSC.	Source Control
9	VCCdig	Supply voltage pin of digital portion of the chip.	Sink Control
10	REFin	Input pin of reference frequency buffer. This pin should be equipped with external 27 MHz oscillator (e.g. TCXO).	9 0 ↓ ESD r=20k ≤ r=20k € idc=9.7u
11	GNDdig	Ground pin of digital portion of the chip.	

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
12	I/Q Balance Control	The voltage on this pin controls the Q channel IF Amplifier Gain. Gain control of ±2 dB can be achieved for 0~3 V. Leave open-circuited if not used. $Q_{gain}$ $\int_{0}^{\frac{1}{2}} \int_{0}^{\frac{1}{2}} \int_{0}^{\frac{1}{2$	
13	PD1	Standby mode control. Low=whole chip OFF & High=Whole chip ON.	
14 15	2IFout-Q 2IFout-Qb	Differential ouptut pins of quadrature demodulator Q output. Adding a lowpass shunt capacitor between these pins will define the IF Bandwidth.	and the second s
16	DC offset Q	DC offset compensation pin for C arm. A low pass capacitor shunt to Pin 17 is required.	280
17	DC offset Qb	DC ottset compensation pin for Q-bar arm. A low pass capacitor shunt to Pin 16 is required.	ido-84u 32

## **UPB1008K**

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit
18	GNDbb	Ground pin of CMOS output driver.	23
19	Qmag	Digitized Q signal. Magnitude bit of 2-bit ADC output.	
20	Qsign	Digitized Q signal. Sign bit of 2-bit ADC output	215
21	Isign	Digitized I signal. Sign bit of 2-bit ADC output.	
22	Imag	Digitized I signal. Magnitude bit of 2-bit ADC output.	
23	VCCbb	Supply voltage pin of CMOS output driver.	₹ r=5k ≹ r=21.5
			180
24	DCoffeetlb	DC offect componention pin for L bar arm	See pin 16 & 17 schematic
24	DConsetio	A low pass capacitor shunt to Pin 25 is required	See pin to a 17 schematic
25	DCoffset	DC offset compensation pin for Larm	-
25	Doonsen	A low pass capacitor shunt to Pin 24 is required	
26	2IFout-lb	Differential output pins of quadrature	See pin 14 & 15 schematic
27	2IFout-I	demodulator Loutput Adding a lownass shunt	
		capacitor between these pins will define the	
		IF bandwidth.	
28	VCC if	Supply voltage pin of analog portion of the chip.	
29	VAGC	Gain control voltage pin of IF amplifier. This voltage	
		performs reverse control,(i.e., VAGC up → gain down).	
		If this pin is left open, then it is default at	
		maximum gain.	The second se
			t = 500 ≤ (=300
			To AGC Amp
		Gain Response	
		0	Ł ESD ∳ r=3k
			I I I
		-15	
			32
		VAGC (V)	
30	IF-in1	Differential input pins of 1st IF AGC amplifier	<sup>28</sup> <b>Q</b>
31	IF-in2		n=4k = n=2k = n=4k
32	GNDanalog	Ground pin of analog portion of the chip.	
			<u>®</u> >q+K →+K →+¬
			Regulator =
			ESD Treak ESD
			ESD A ESD
			r=1.42k r=1.42k
			32 🔂
			10
33	Mixout2	Differential output pins of RF mixer. This is an emitter	
34	Mixout1	follower output buffer, provide a 50 $\Omega$ output load.	
			r=111 🛔
			4 <b>0</b>

Pin No.	Symbol	Function and Application	Internal Equivalent Circuit		
35	Vref	Base-emitter junction voltage wth respect to ground. May be used for biasing an external discrete transistor. Regulation will develop PTAT current.	Regulator GND 4 4 4 1 4 1 4 1 1 1 1 1 1 1 1 1 1 1 1 1		
36	LNAbias	LNA output pin. External bias (Vcc) and matching for gain is required.	See pin 2 schematic		

## **INTERNAL BLOCK DIAGRAM**



### ORDERING INFORMATION

Part Number	Package
UPB1008K-A	36 Pin plastic QFN

### OUTLINE DIMENSIONS (Units in mm)



#### Caution:

The island pins located on the corners are needed to fabricate products in our plant, but do not serve any other function.

Consequently the island pins should not be soldered and should remain non-connection pins.

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)
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Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
РВВ	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

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